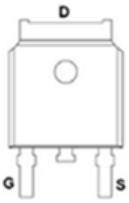
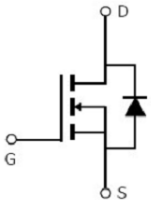
Main Product Characteristics:

V_{DSS}	30V
R_{DS}(on)	2.3mΩ(typ.)
I_D	110A ①

TO-252



Pin Assignment



Schematic Diagram

Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150℃ operating temperature

Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute Max Rating:

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V ①	110	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V ①	68	
I_{DM}	Pulsed Drain Current ②	192	
P_D @T_C = 25°C	Power Dissipation ③	62.5	W
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy @ L=0.1mH	144.7	mJ
I_{AS}	Avalanche Current @ L=0.1mH	53.8	A
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +150	°C

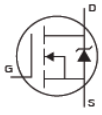
Thermal Resistance

Symbol	Characteristics	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	2.4	℃/W
$R_{\theta JA}$	Junction-to-ambient (t ≤ 10s) ④	—	25	℃/W
	Junction-to-Ambient (PCB mounted, steady-state)④	—	62	℃/W

Electrical Characteristics @T_A=25℃unless otherwise specified

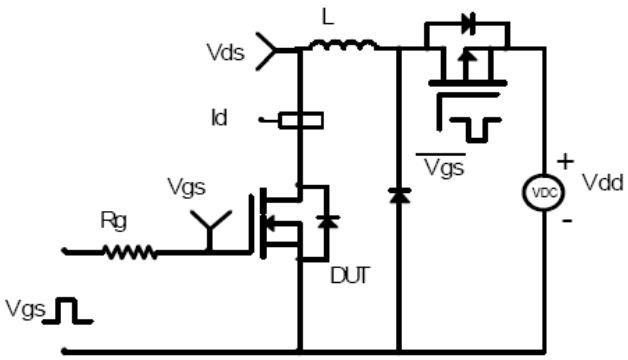
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	30	—	—	V	V_{GS} = 0V, I_D = 250μA
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	2.3	4	mΩ	V_{GS}=10V,I_D =30A
		—	4.3	6		V_{GS}=4.5V,I_D =15A
$V_{GS(th)}$	Gate threshold voltage	1.2	1.6	2.5	V	V_{DS} = V_{GS}, I_D = 250μA
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	V_{DS} =24V,V_{GS} = 0V
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	V_{GS} =20V
		—	—	-100		V_{GS} = -20V
Q_g	Total gate charge	—	68	—	nC	I_D = 15A,
Q_{gs}	Gate-to-Source charge	—	10	—		V_{DS}=15V,
Q_{gd}	Gate-to-Drain("Miller") charge	—	15	—		V_{GS} = 4.5V
$t_{d(on)}$	Turn-on delay time	—	10	—	ns	V_{GS}=10V, V_{DS} =15V, R_{GEN}=3.3Ω,I_D =15A
t_r	Rise time	—	118	—		
$t_{d(off)}$	Turn-Off delay time	—	22	—		
t_f	Fall time	—	58	—		
C_{iss}	Input capacitance	—	3480	—	pF	V_{GS} = 0V
C_{oss}	Output capacitance	—	380	—		V_{DS} = 15V
C_{rss}	Reverse transfercapacitance	—	350	—		ƒ = 1MHz

Source-Drain Ratings and Characteristics

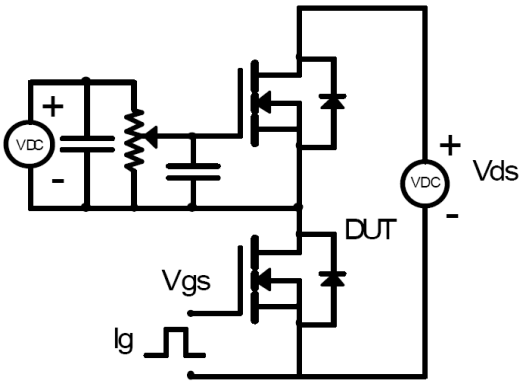
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode) ①	—	—	90	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	360	A	
V_{sd}	Diode Forward Voltage	—	—	1.2	V	I_S=1A, V_{GS}=0V

Test circuits and Waveforms

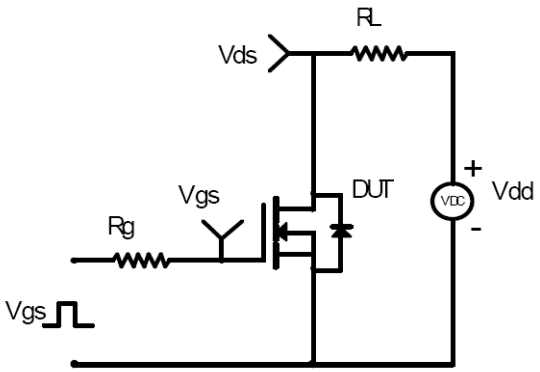
EAS Test Circuit:



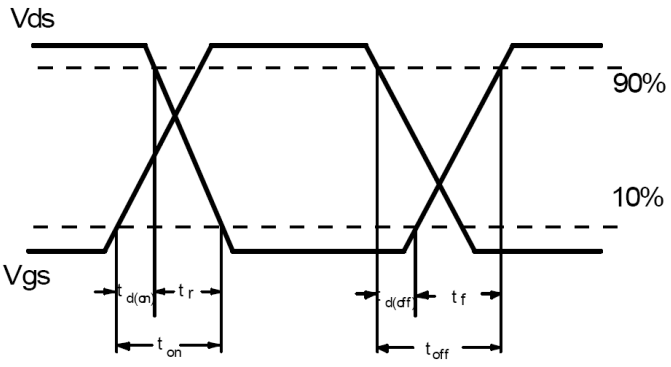
Gate charge test circuit:



Switching Time Test Circuit:



Switching Waveforms:



Notes:

①Calculated continuous current based on maximum allowable junction temperature.

②Repetitive rating; pulse width limited by max. junction temperature.

③The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.

④The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with TA =25°C

Typical electrical and thermal characteristics

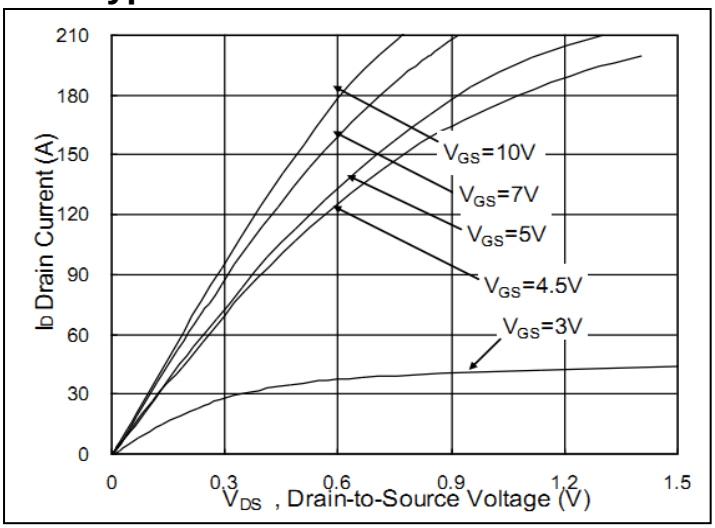


Figure 1.Typical Output Characteristics

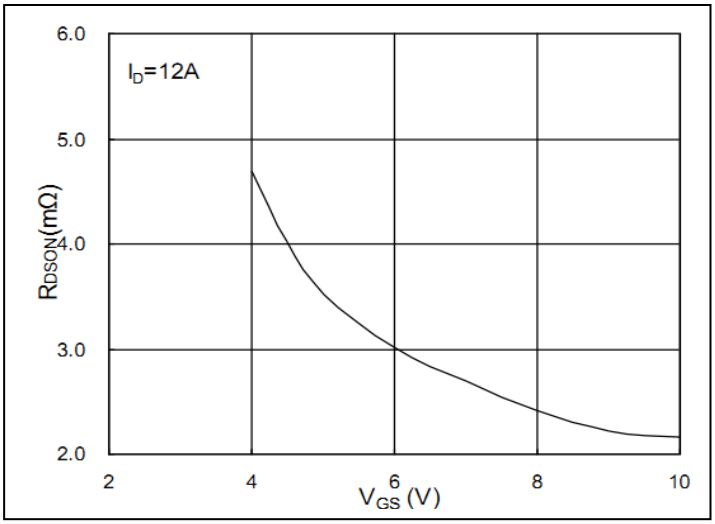


Figure 2. Rdson vs. G-S Voltage

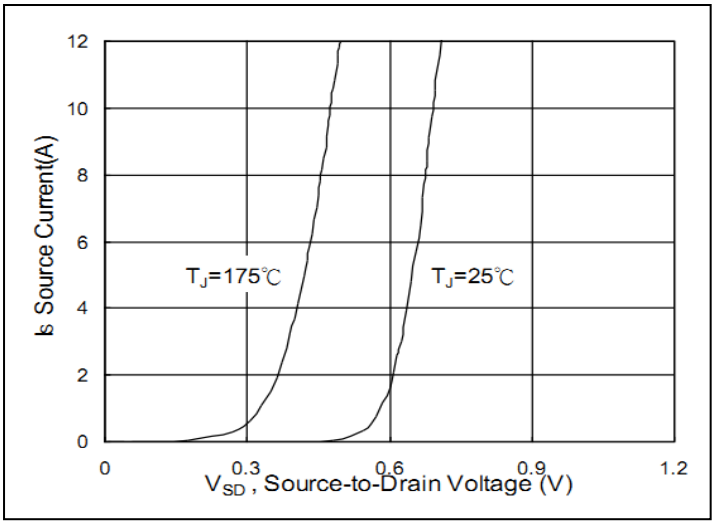


Figure 3. Forward Characteristics Of Reverse

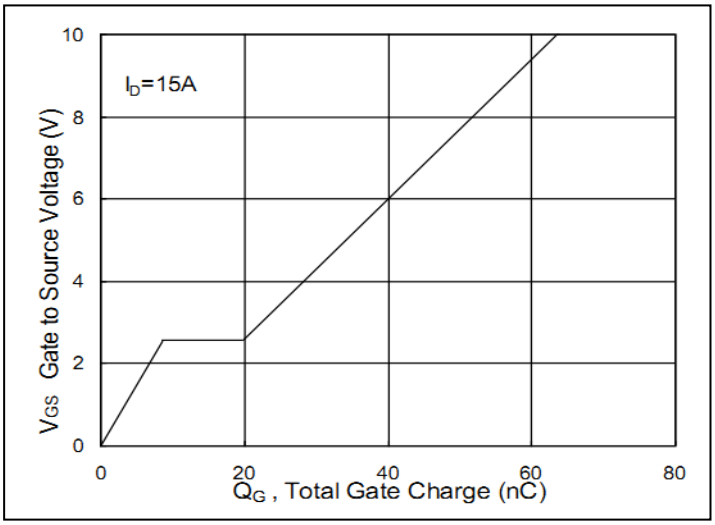


Figure 4.Gate Charge

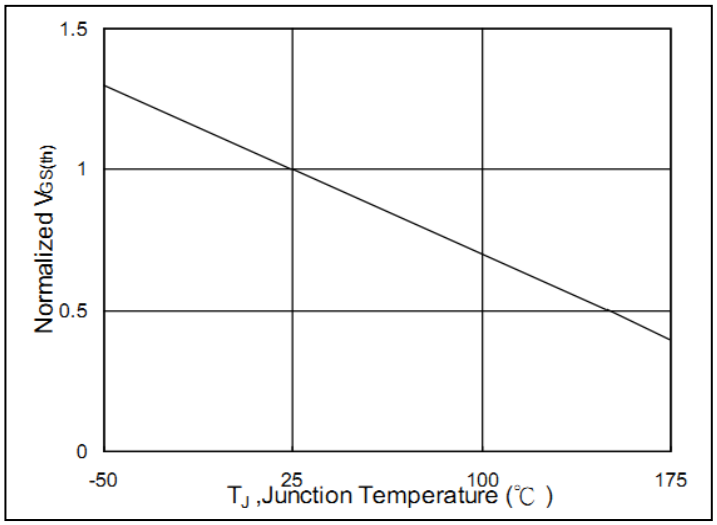


Figure5. Normalized V_{GS}(th) vs Junction Temperature

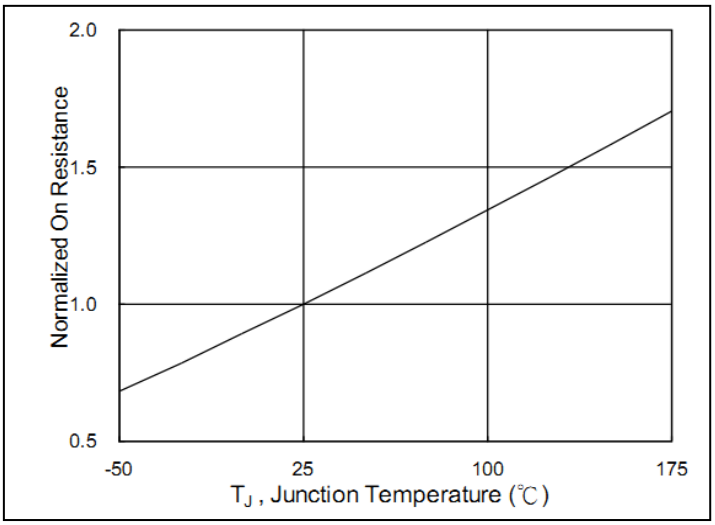


Figure6. Normalized On-Resistance vs. Junction Temperature

Typical electrical and thermal characteristics

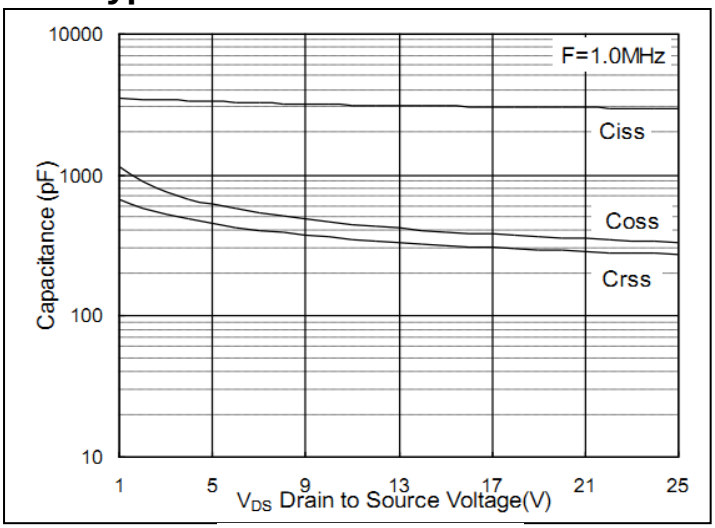


Figure7. Capacitance

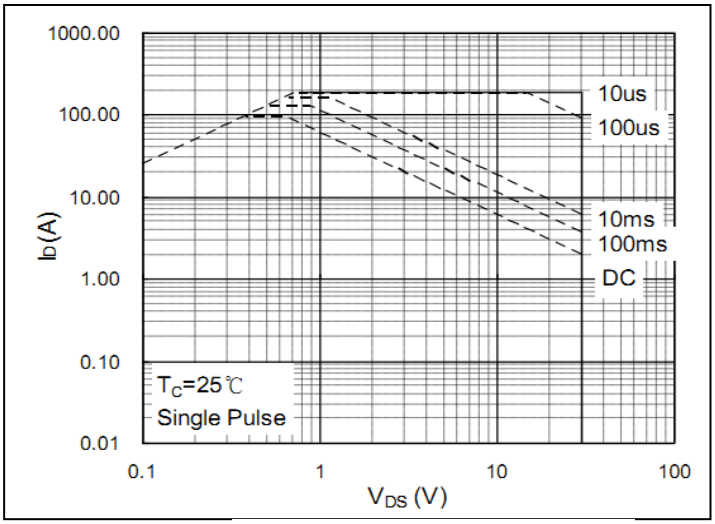


Figure8. Safe Operation Area

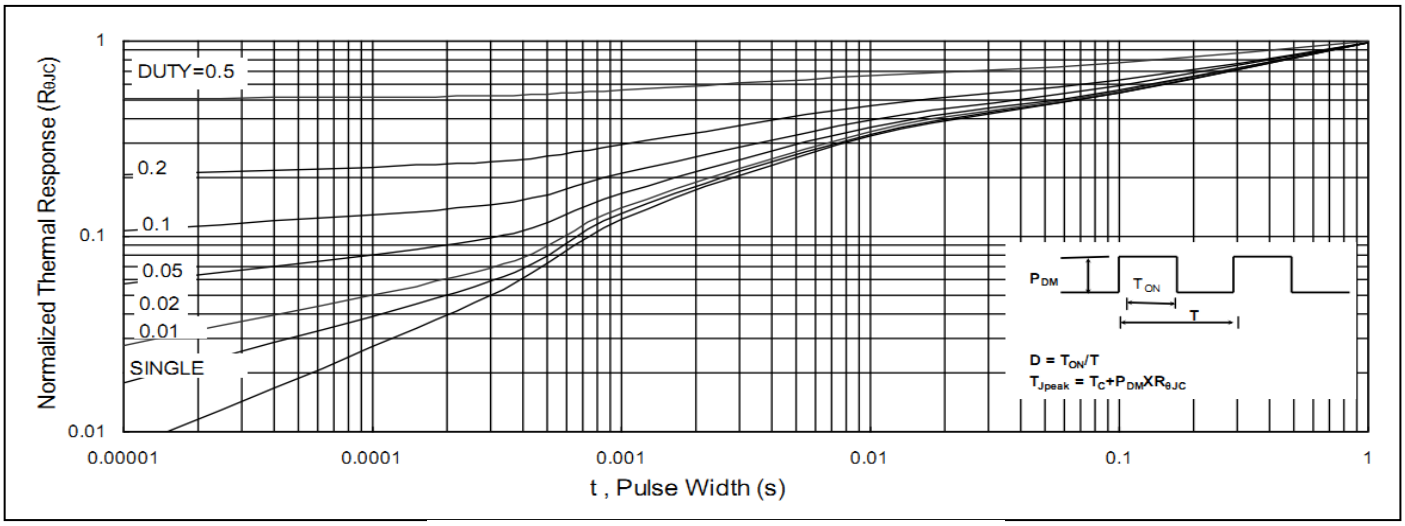
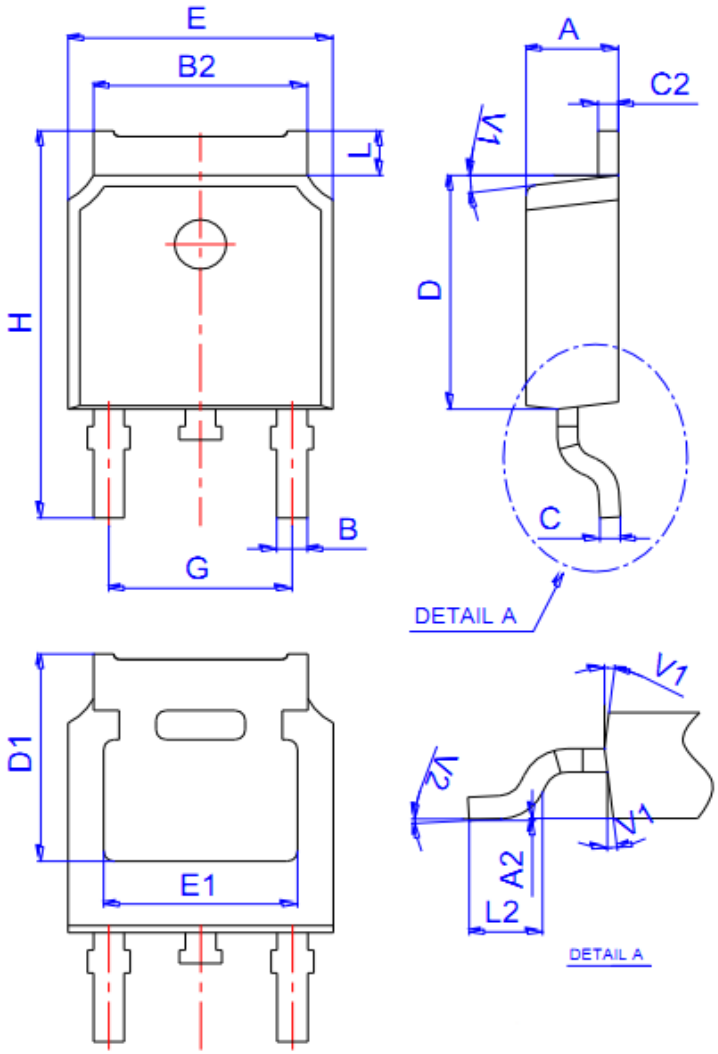


Figure9. Transient Thermal Impedance

Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

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